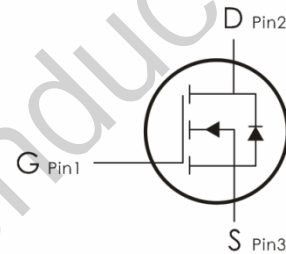


Description:

This N-Channel MOSFET uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge. It can be used in a wide variety of applications.

Features:

- 1) $V_{DS}=60V, I_D=68A, R_{DS(ON)} < 10m\Omega @ V_{GS}=10V$
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density trench technology for ultra $R_{DS(ON)}$.
- 5) Excellent package for good heat dissipation.



Absolute Maximum Ratings: ($T_C=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current- $T_C=25^\circ C^1$	68	A
	Continuous Drain Current- $T_C=100^\circ C$	---	
	Pulsed Drain Current ²	204	
E_{AS}	Single Pulse Avalanche Energy ⁴	91	mJ
P_D	Power Dissipation, $T_C=25^\circ C$	81	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ C$

Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.54	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient ⁵	62	

Electrical Characteristics: ($T_c=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\ \mu\text{A}$	60	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS}=0V, V_{DS}=60V$	---	---	1	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0A$	---	---	± 100	nA
On Characteristics						
$V_{GS(th)}$	GATE-Source Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\ \mu\text{A}$	1	---	2.5	V
$R_{DS(on)}$	Drain-Source On Resistance	$V_{GS}=10V, I_D=20A$	---	7.5	10	m Ω
		$V_{GS}=4.5V, I_D=10A$	---	10	13	
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=50V, V_{GS}=0V, f=1\text{MHz}$	---	1204	---	pF
C_{oss}	Output Capacitance		---	194.1	---	
C_{rss}	Reverse Transfer Capacitance		---	9.9	---	
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{DD}=50V, I_D=25A,$ $V_{GS}=10V, R_{GEN}=3\Omega$	---	23.9	---	ns
t_r	Rise Time		---	4.6	---	ns
$t_{d(off)}$	Turn-Off Delay Time		---	37.8	---	ns
t_f	Fall Time		---	6.4	---	ns
Q_g	Total Gate Charge	$V_{GS}=10V, V_{DS}=50V,$ $I_D=25A$	---	17.9	---	nC
Q_{gs}	Gate-Source Charge		---	3.8	---	nC
Q_{gd}	Gate-Drain "Miller" Charge		---	4.2	---	nC
Drain-Source Diode Characteristics						
V_{SD}	Source-Drain Diode Forward Voltage	$V_{GS}=0V, I_S=20A$	---	---	1.3	V
I_S	Continuous Source Current	$V_{GS}<V_{th}$	---	---	68	A

trr	Reverse Recovery Time	$I_S=25\text{ A}$, $di/dt=100\text{ A}/\mu\text{s}$	36.3	---	Ns
qrr	Reverse Recovery Charge		1.4	---	nc

Notes:

- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3) Pd is based on max. junction temperature, using junction-case thermal resistance.
- 4) $V_{DD}=30\text{ V}$, $R_G=50\ \Omega$, $L=0.3\text{ mH}$, starting $T_J=25\ ^\circ\text{C}$.
- 5) The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_a=25\ ^\circ\text{C}$.

Typical Characteristics: ($T_C=25\ ^\circ\text{C}$ unless otherwise noted)

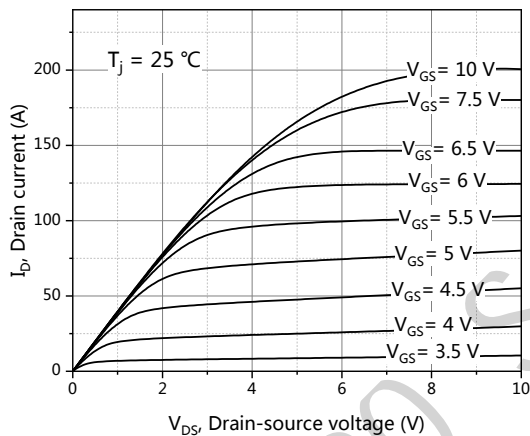


Figure 1, Typ. output characteristics

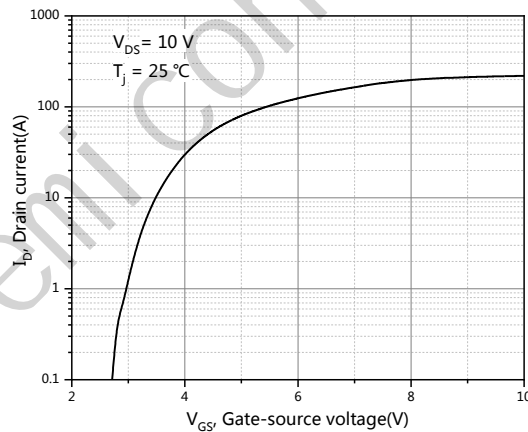


Figure 2, Typ. transfer characteristics

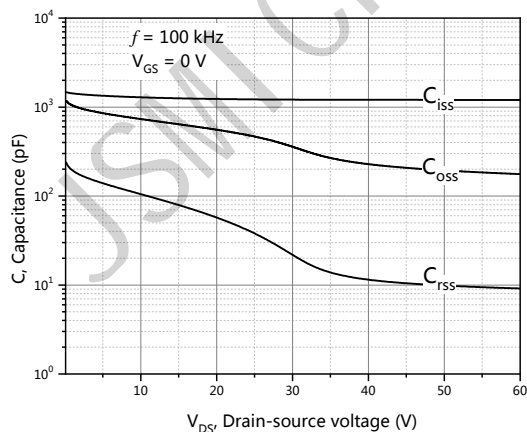


Figure 3, Typ. capacitances

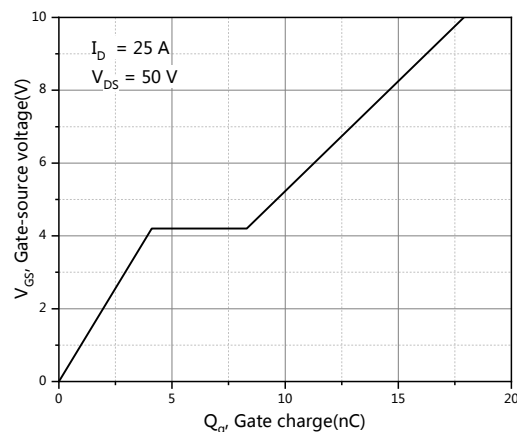


Figure 4, Typ. gate charge

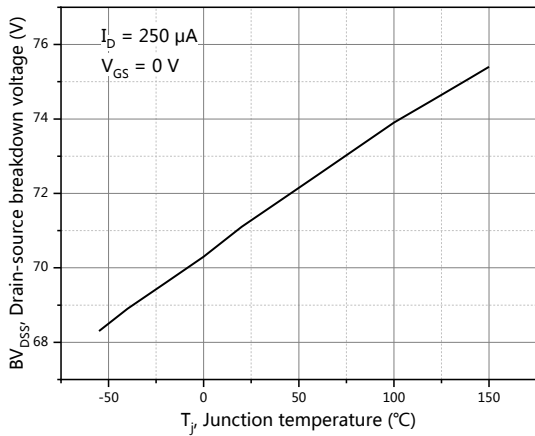


Figure 5, Drain-source breakdown voltage

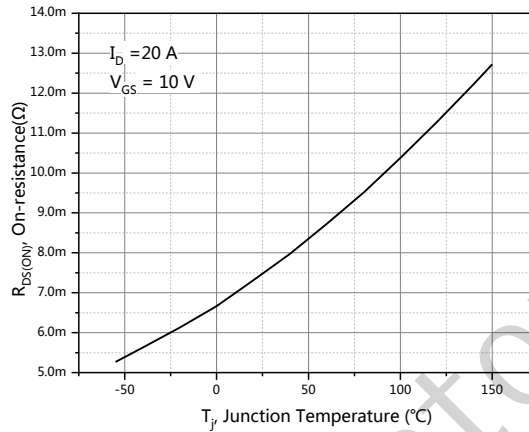


Figure 6, Drain-source on-state resistance

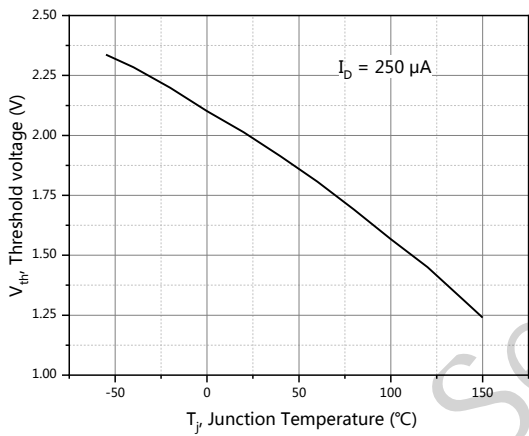


Figure 7, Threshold voltage

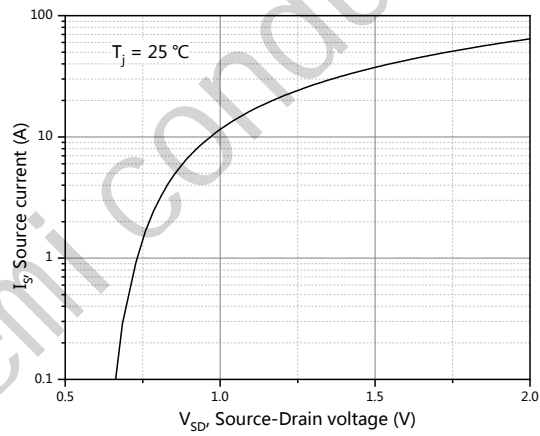


Figure 8, Forward characteristic of body diode

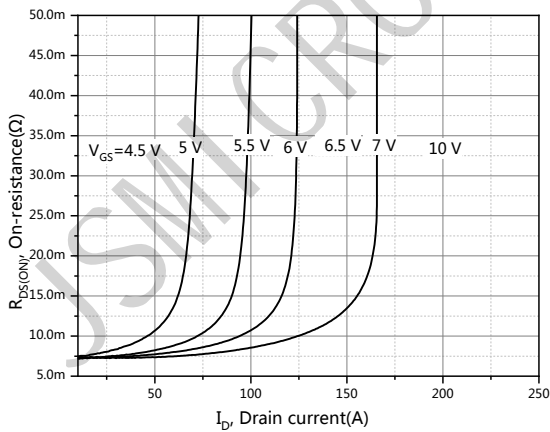


Figure 9, Drain-source on-state resistance

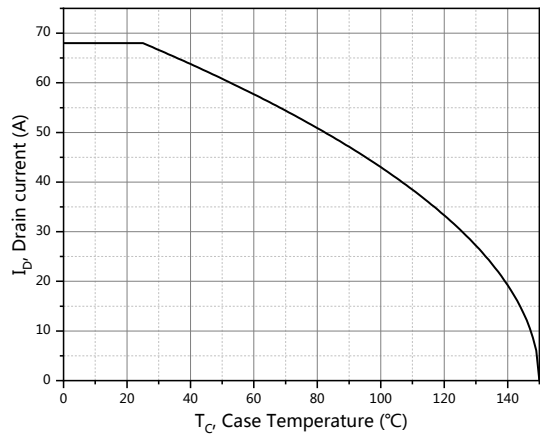


Figure 10, Drain current

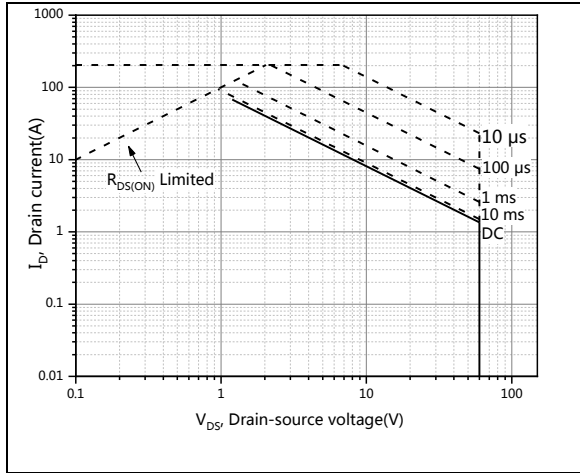


Figure 11, Safe operation area $T_C=25\text{ }^\circ\text{C}$

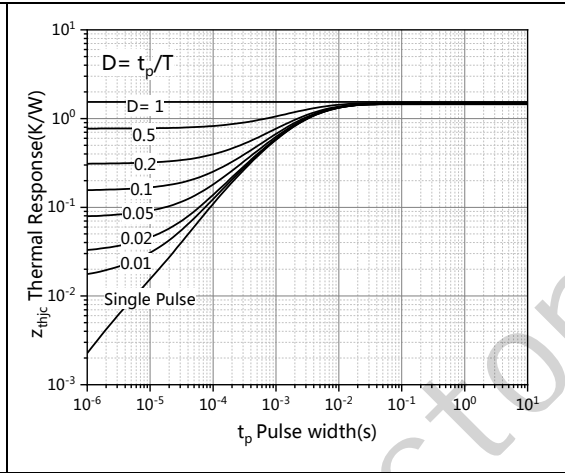


Figure 12, Max. transient thermal impedance

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